

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (currently amended) ~~A~~The flame hydrolysis process for the manufacture of glass bodies of doped silica glass, wherein a first formed glass body is generated on a target by flame hydrolysis using a single burner into which fuel and precursors are fed for generating the doped silica glass, of Claim 27, wherein at least titanium is used as a dopant, and wherein said first formed glass body is subsequently reheated in a mold to a temperature above the glass transition temperature for reshaping the first formed glass body into a second formed body having a larger breadth and a smaller height than said first formed glass body.

2. (cancelled)

3. (previously presented) The process of claim 1, wherein a further dopant is added that comprises at least one component selected from the group formed by fluorine, germanium, vanadium, chromium, aluminum, zirconium, iron, zinc, tantalum, boron, phosphorus, niobium, lead, hafnium, molybdenum and tungsten.

4. (cancelled)

5. (previously presented) The process of claim 1, wherein said precursors fed into said burner are selected to yield a dopant concentration in said first formed glass body of at least 0.1 wt.-%.

6. (previously presented) The process of claim 1, wherein said precursors fed into said burner are selected to yield a dopant concentration in said first formed glass body of at least 0.5 wt.-%.

7. (original) The process of claim 1, wherein said precursors fed into said burner are selected to yield a dopant concentration in said first formed glass body of at least 1 wt.-%.

8. (previously presented) The process of claim 3, wherein said further dopant comprises at least 0.005 wt.-% of fluorine.

9. (previously presented) The process of claim 3, wherein said further dopant comprises at least 0.01 wt.-% of fluorine.

10. (original) The process of claim 1, wherein said target is rotatably driven while said first formed glass body is formed.

11. (original) The process of claim 10, wherein there is a distance between said first formed glass body and said burner that is kept substantially constant during generation of said first formed glass body.

12. (currently amended) The process of claim 10, wherein said target is arranged substantially horizontally and below said burner, and wherein said first formed glass body is grown substantially in a vertical direction.

13. (original) The process of claim 10, wherein said target is arranged substantially vertically and said first formed glass body is grown substantially in a horizontal direction.

14. (cancelled)

15. (original) The process of claim 1, wherein a disk comprising doped silica glass is used as the target.

16. (original) The process of claim 1, wherein said reshaping step is followed by at least one further reshaping step.

17. (withdrawn) A glass body of doped silica glass comprising striae having thicknesses of ≤ 70 micrometers.

18. (withdrawn) The glass body of claim 17, wherein said striae have thicknesses of ≤ 40 micrometers.

19. (withdrawn) The glass body of claim 17, wherein said striae have thicknesses of ≤ 20 micrometers.

20. (withdrawn) The glass body of claim 17, wherein said striae have thicknesses of ≤ 15 micrometers.

21. (withdrawn) A glass body of doped silica glass comprising defects, said defects having a defect density of no more than 50 defects per square centimeter, with a given defect detection sensitivity for defects of at least 200 nanometers diameter.

22. (withdrawn) The glass body of claim 21, wherein the defect density is no more than 25 defects per square centimeter.

23. (withdrawn) The glass body of claim 21, wherein the defect density is no more than 10 defects per square centimeter.

24. (withdrawn) The glass body of claim 19, further comprising defects, said defects having a defect density of no more than 25 defects per square centimeter, with a given defect detection sensitivity for defects of at least 200 nanometers diameter.

25. (withdrawn) An EUV lithography component comprising a glass body according to claim 24.

26. (cancelled)

27. (previously presented) A flame hydrolysis process for the manufacture of glass bodies of doped silica glass, wherein a first formed glass body is generated on a target by flame hydrolysis using a single burner into which fuel and precursors are fed

for generating the doped silica glass, wherein a dopant is used that comprises at least one component selected from the group formed by titanium, fluorine, germanium, vanadium, chromium, aluminum, zirconium, iron, zinc, tantalum, boron, phosphorus, niobium, lead, hafnium, molybdenum and tungsten, wherein said first formed body is subsequently reheated in a mold to a temperature above the glass transition temperature for reshaping the first formed body into a second formed body having a larger breadth and a smaller height than said first glass body, wherein said first formed glass body is formed through an opening of a furnace muffle while keeping a distance of about 10 to 20 mm between a flame outer rim and a refractory material of said furnace muffle.

28. (previously presented) The flame hydrolysis process of claim 27, wherein a burner hole is used that is configured gradually conically shaped and opening gradually with an angle of 10 to 20 °.

29. (cancelled)

30. (cancelled)

31. (new) The flame hydrolysis process of claim 28, wherein said first glass body is formed through said opening of said furnace muffle while keeping a constant distance between said single burner and a particle generation point on said target.

32. (new) The flame hydrolysis process of claim 31, wherein said distance between said single burner and said particle generation point on said target is kept constant between 150 and 250 millimeters.

33. (new) The flame hydrolysis process of claim 28, wherein said target is arranged substantially horizontally and below said burner, and wherein said first formed body is grown substantially in vertical direction.